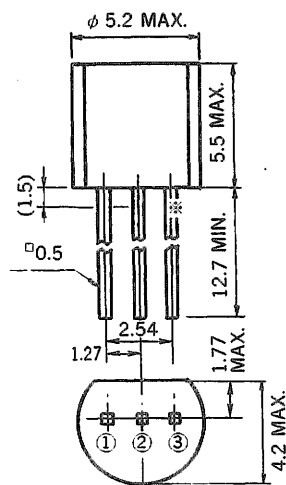


(Unit : mm)



※ Measure point of Case Temperature

ITEM	SYMBOL	MAXIMUM RATINGS	UNIT	NOTE
Repetitive Peak off Voltage	V_{DRM}	400	V	
Non-repetitive Peak off Voltage	V_{DSM}	500	V	
RMS On-State Current	$I_T(RMS)$	0.8 ($T_C = 68^\circ C$)	A	Fig. 12, 13
Peak Surge On-State Current	I_{TSM}	7 (50 Hz), 8 (60 Hz)	A	Fig. 2
Fusing Current	$\int i^2 T dt$	0.2 (1 ms $\leq t \leq 10$ ms)	A ² s	
Peak Gate Power Dissipation	P_{GM}	1	W	
Average Gate Power Dissipation	$P_{G(AV)}$	0.1	W	
Peak Gate Current	I_{GM}	± 1	A	
Junction Temperature	T_j	125	$^\circ C$	
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$	

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$)

ITEM		SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	NOTE
Peak Off-State Current		I_{DRM}	$V_{\text{DM}} = V_{\text{DRM}}$	$T_{\text{J}} = 25\text{ }^{\circ}\text{C}$	—	—	10	μA	
				$T_{\text{J}} = 125\text{ }^{\circ}\text{C}$	—	—	100		
On-State Voltage		V_{TM}	$I_{\text{TM}} = 1.2\text{ A}$		—	—	1.5	V	Fig. 1
Critical Rate of Rise of Off-State Voltage		dv/dt	$T_{\text{J}} = 125\text{ }^{\circ}\text{C}$, $V_{\text{DM}} = \frac{2}{3} V_{\text{DRM}}$ Gate Open Circuited Exponential Waveform		—	50	—	V/ μs	
*DC Gate Trigger Current	MODE I	I_{GT}	$V_{\text{DM}} = 12\text{ V}$ $R_{\text{L}} = 100\text{ }\Omega$	G; Positive, T_2 ; Positive	—	—	5	mA	Fig. 4, 5
	II			G; Negative, T_2 ; Positive	—	—	10		
	III			G; Negative, T_2 ; Negative	—	—	5		
	IV			G; Positive, T_2 ; Negative	—	—	10		
DC Gate Trigger Voltage	MODE I	V_{GT}	$V_{\text{DM}} = 12\text{ V}$ $R_{\text{L}} = 100\text{ }\Omega$	G; Positive, T_2 ; Positive	—	—	1.0	V	Fig. 4, 5
	II			G; Negative, T_2 ; Positive	—	—	1.5		
	III			G; Negative, T_2 ; Negative	—	—	1.0		
	IV			G; Positive, T_2 ; Negative	—	—	1.5		
Gate Non-Trigger Voltage		V_{GD}	$T_{\text{J}} = 125\text{ }^{\circ}\text{C}$ $V_{\text{DM}} = \frac{1}{2} V_{\text{DRM}}$		0.1	—	—	V	
DC Holding Current		I_{H}	$V_{\text{D}} = 24\text{ V}$, $I_{\text{TM}} = 1\text{ A}$		—	5	10	mA	
Critical Rate of Rise of Commutating Off-State Voltage		$(dv/dt)_{\text{c}}$	$T_{\text{J}} = 125\text{ }^{\circ}\text{C}$, $I_{\text{TM}} = 1.2\text{ A}$ $(di_{\text{T}}/dt)_{\text{c}} = -0.5\text{ A/ms}$ $V_{\text{DM}} = 400\text{ V}$		1	—	—	V/ μs	
Steady State		$R_{\text{th(j-c)}}$	Junction to Case		—	—	65	$^{\circ}\text{C/W}$	
Thermal Resistance		$R_{\text{th(j-a)}}$	Junction to Ambient		—	—	200	$^{\circ}\text{C/W}$	Fig. 14

* All four quadrants: 5 mA Max. Selected types available from factory.

Fig. 1 $i_T - V_T$ CHARACTERISTIC

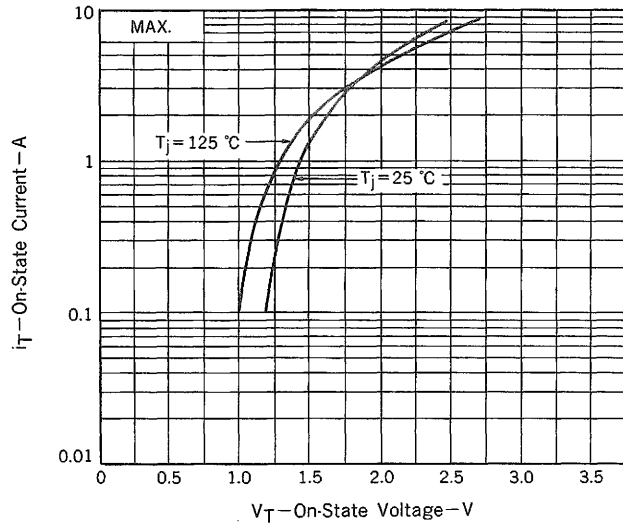


Fig. 2 I_{TSM} RATING

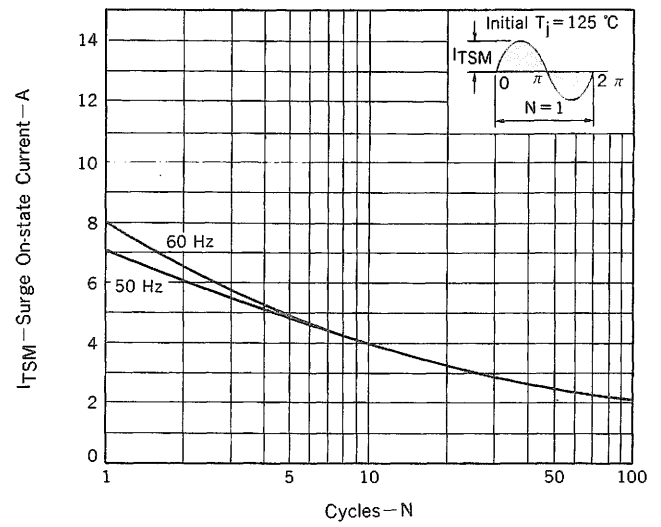


Fig. 3 $V_G - I_G$ RATING

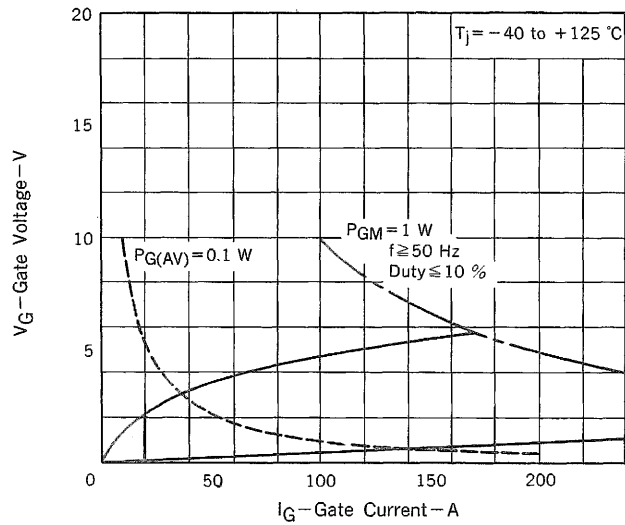


Fig. 4 GATE CHARACTERISTIC

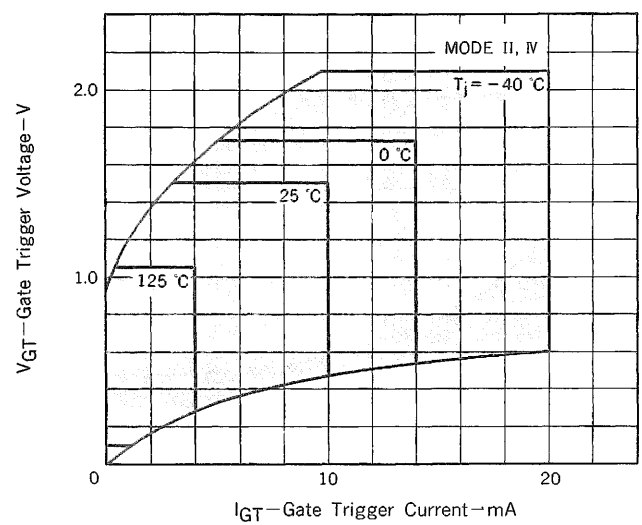


Fig. 5 GATE CHARACTERISTIC

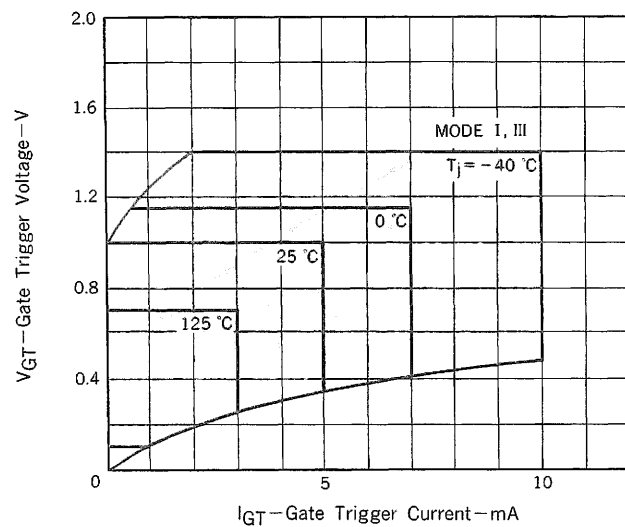


Fig. 6 $I_{GT} - T_a$ TYPICAL DISTRIBUTION

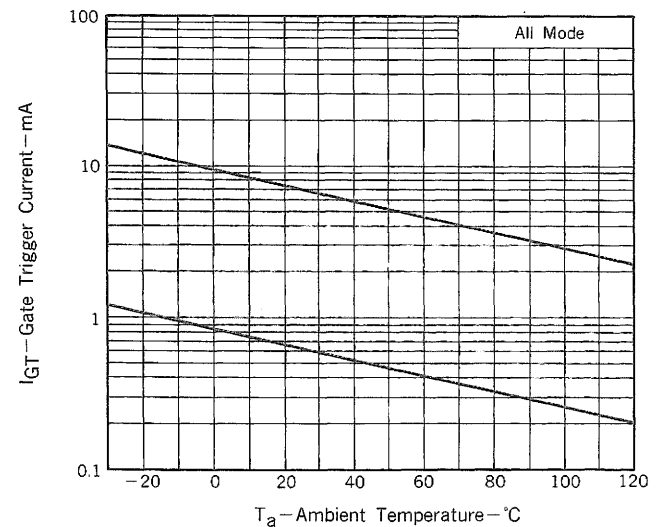


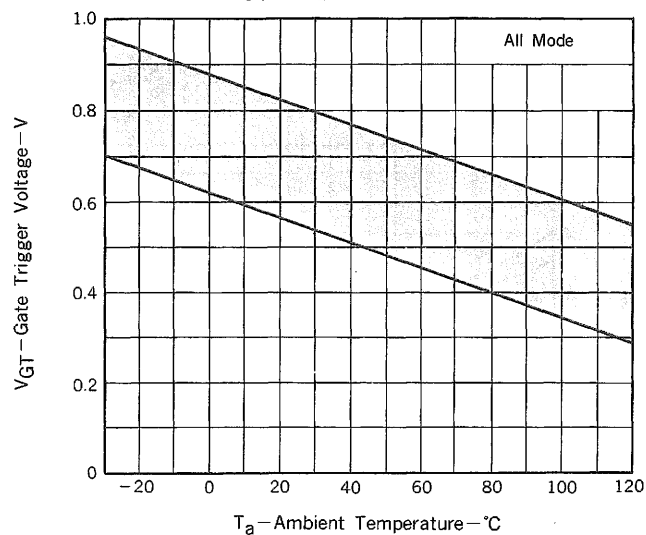
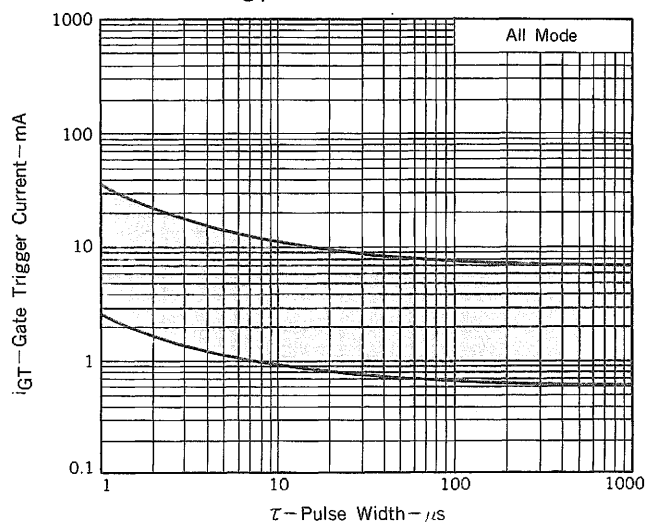
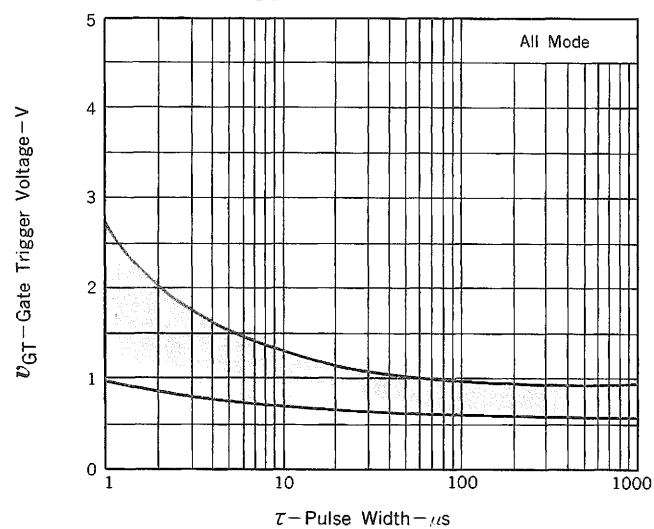
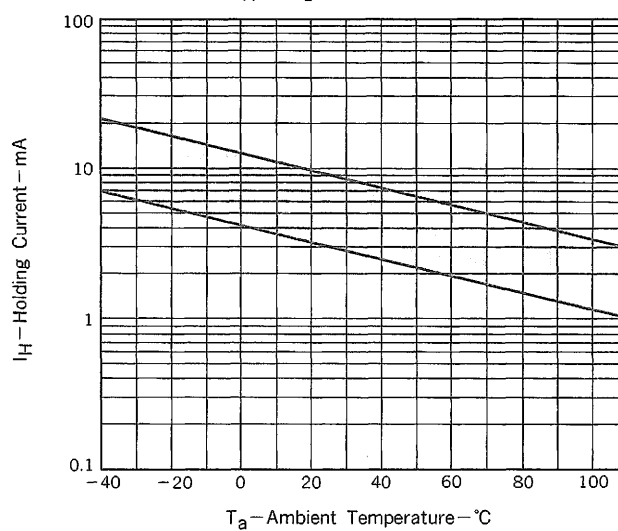
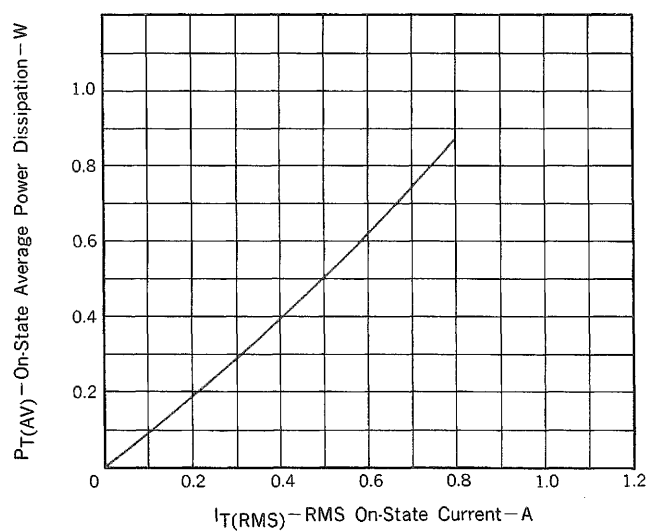
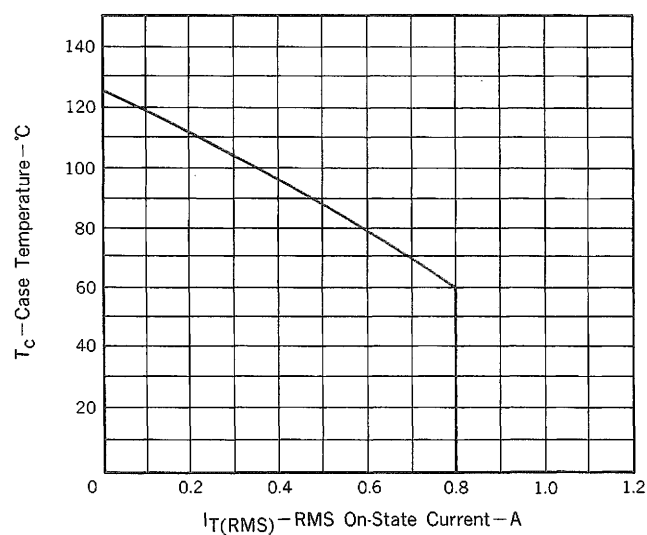
Fig. 7 $V_{GT} - T_a$ TYPICAL DISTRIBUTIONFig. 8 $i_{GT} - \tau$ TYPICAL DISTRIBUTIONFig. 9 $v_{GT} - \tau$ TYPICAL DISTRIBUTIONFig. 10 $I_H - T_a$ TYPICAL DISTRIBUTIONFig. 11 $P_{T(AV)} - I_{T(RMS)}$ CHARACTERISTICFig. 12 $T_c - I_{T(RMS)}$ RATING

Fig. 13 $T_a - I_T(\text{RMS})$ RATING

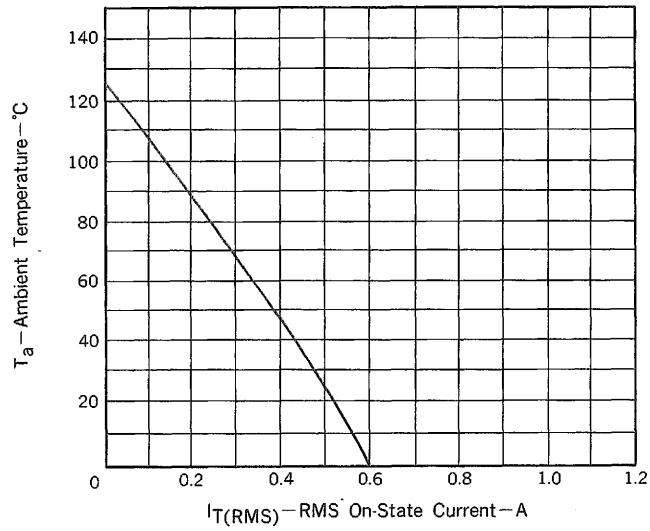


Fig. 14 Z_{th} CHARACTERISTIC

